

A METHOD AND APPARATUS FOR FORMING A SILICON WAFER WITH A DENUDED ZONE

Abstract of the Invention

5 An apparatus and method are provided for forming an epitaxial layer on and denuded zone in a semiconductor wafer used in manufacturing electronic components. The denuded zone and epitaxial layer are formed in one apparatus. The apparatus includes a Bernoulli wand that is used to support the wafer in a cooling position to effect fast cooling of the wafer and formation of the denuded zone.